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**DETECTOR FOR SHORT WAVE FIBER OPTIC COMMUNICATIONS WITH
COMPENSATION TO REDUCE DETECTOR JITTER**

Related Applications

5 Related United States patent applications assigned to the present
assignee are being filed on the same day as the present patent application
including:

 United States patent application Serial Number _____,
entitled "FIBER OPTIC TRANSCEIVER ARRAY FOR IMPLEMENTING
TESTING" by Randolph B. Heineke and David W. Siljenberg; and

10 United States patent application Serial Number _____,
entitled " FIBER OPTIC TRANSCEIVER ARRAY AND FIBER OPTIC
TRANSCEIVER CHANNEL FOR SHORT WAVE FIBER OPTIC
COMMUNICATIONS " by Randolph B. Heineke and David John Orser.

Field of the Invention

15 The present invention relates generally to the communications field,
and more particularly, relates to a detector for short wave fiber optic
communications having compensation to reduce detector jitter.

Description of the Related Art

20 Demand for bandwidth in data communications appears to be
generally unlimited. One of the economic considerations to meet this

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demand is to minimize the physical size of fiber optic transceivers. One known arrangement uses an array of integrated photodetector and preamplifiers to reduce the number of components and connections in the fiber optic transceivers and gain benefits of compactness.

5 Photodetectors can be vertical or lateral structures. Lateral structures are more attractive to integrate. Vertical structures have better jitter characteristics. Lateral structures can be formed using the same processing steps as accompanying analog circuitry. Vertical detectors alone require specialized processing steps. Integrating vertical structures with analog
10 circuitry is unattractive due to the processing steps required and attendant increased manufacturing cost. This is especially true for larger array chip sizes and the attendant yields of larger array chips.

15 In the lateral photodetector, jitter is most significant constraint on high speed operation. Lateral photodetector jitter is largely a result of the photodetector geometry. On the surface the lateral detector has excellent high speed characteristics, the fields to sweep photo carriers to the collecting points are strong and the carriers are quickly removed. However, photons that penetrate more deeply generate photo carriers that encounter weaker fields and are collected more slowly. Other mechanisms that lead to
20 jitter can include trap states and photo carrier generation in undepleted regions.

 A need exists for a detector for short wave fiber optic communications having compensation to reduce detector jitter. Compensating for lateral photodetector jitter is particularly desirable for a fiber optic transceiver array.

25 **Summary of the Invention**

 A principal object of the present invention is to provide a detector for short wave fiber optic communications having compensation to reduce detector jitter. Other important objects of the present invention are to provide such detector for short wave fiber optic communication having
30 compensation to reduce detector jitter substantially without negative effect and that overcome many of the disadvantages of prior art arrangements.

In brief, a detector is provided for short wave fiber optic communications having compensation to reduce detector jitter. The detector includes a photodetector providing a modulated current. A transimpedance amplifier is coupled to the photodetector receiving the modulated current and providing an output voltage signal. An output buffer is coupled to the transimpedance amplifier receiving the output voltage signal. The output buffer includes a differential transistor pair; a pair of source degeneration resistors connected to the differential transistor pair; and a capacitor coupled between connections of the differential transistor pair and the source degeneration resistors. The value of the capacitor coupled between connections of the differential transistor pair and the source degeneration resistors is selected to reduce jitter.

In accordance with features of the invention, the capacitor passes high slew rate transimpedance amplifier output voltage signals more readily than low slew rate transimpedance amplifier output voltage signals. The effect of the capacitor is to bypass the gain limiting effects of the source degeneration resistors. As a result the differential transistor pair accentuates high slew rates over lower ones so that detector jitter is reduced.

Brief Description of the Drawings

The present invention together with the above and other objects and advantages may best be understood from the following detailed description of the preferred embodiments of the invention illustrated in the drawings, wherein:

FIG. 1 is a schematic and block diagram illustrating a detector for short wave fiber optic communications in accordance with the preferred embodiment; and

FIG. 2 is a schematic diagram illustrating output buffer circuitry of the detector for short wave fiber optic communications of FIG. 1 in accordance with the preferred embodiment.

Detailed Description of the Preferred Embodiments

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Having reference now to the drawings, in FIG. 1, there is shown a detector for short wave fiber optic communications generally designated by the reference character 100 in accordance with the preferred embodiment. Fiber optic communications detector 100 of the preferred embodiment
5 includes compensation to reduce detector jitter.

Fiber optic communications detector 100 includes a photodetector 102 biased by a source current source 104 and a sink current source 106. Photodetector 102 of the preferred embodiment is a lateral structure, such as a lateral PIN photodiode structure. Photodetector 102 detects a light
10 input applied, for example, via an optical fiber (not shown) and provides a modulated current output. Modulated current is fed to a transimpedance amplifier (TIA) 108 via a pair of capacitors 110, 112. Capacitors 110, 112 are AC coupling capacitors adapted for passing high frequency and blocking low frequency signals. Transimpedance amplifier (TIA) 108 provides a
15 voltage signal output indicated at lines labeled IN and INC. The voltage output IN and INC of the transimpedance amplifier 108 is applied to an output buffer stage 118. The output buffer 118 the preferred embodiment provides compensation to reduce detector jitter of the lateral photodetector 102. The output buffer 118 the preferred embodiment is illustrated and
20 described with respect to FIG. 2.

Differential outputs OUT, OUTC from the buffer stage 118 are connected to an electrostatic discharge (ESD) channel protection circuit 120. ESD channel protection circuit 120 includes a plurality of metal
semiconductor field effect transistors (MESFETs) 122, 124, 126 and 128, as
25 shown. MESFETs 122, 124, 126 and 128 have a diode arrangement for implementing ESD protection of the outputs OUT, OUT_C from the buffer stage 118. A respective output OUT, OUTC from the buffer stage 118 is applied to a respectively applied to a gate input of metal semiconductor field effect transistors (MESFETs) 122, 126 and respectively applied to a drain
30 input of MESFETs 124, 128 having a gate input connected to ground. A drain of NFETs 122 and 124 is connected to a high voltage supply Vdd. The respective drain and source of MESFETs 122, 124, 126 and 128 are connected together.

In accordance with features of the preferred embodiment, some of the

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repeatable portion of the photodetector jitter is effectively removed. The response of a lateral photodetector 102 is at first very sudden but incomplete. The slow carriers, which arrive later, eventually add to the response. Fiber optic communications detector 100 emphasizes sudden rises and falls of photocurrent while providing less emphasis on lower slow rates to remove jitter. The output buffer 118 of the preferred embodiment of the fiber optic transceiver channel 100 provides effective compensation for effectively minimizing or removing the photodetector jitter.

Referring now to FIG. 2, the output buffer 118 of the fiber optic transceiver channel 100 is shown. A channel decoupling capacitor 200 is strategically positioned relative to the channel differential outputs OUT and OUTC of the output buffer stage 118 for power noise sensitivity reduction. The output buffer stage 118 is operated differentially to reduce generation of and susceptibility to noise.

An input stage of the buffer stage 118 consists of a differential transistor pair 202. Differential transistor pair 202 is defined by a pair of metal semiconductor field effect transistors (MESFETs) 204 and 206. Differential transistor pair 202 is a high gain amplifier adapted for providing detector jitter compensation. Output buffer stage 118 receives voltage inputs IN and INC respectively applied to a gate input the of high gain metal semiconductor field effect transistors (MESFETs) 204 and 206.

Input stage differential transistor pair 202 of MESFETs 204 and 206 includes a pair of source degeneration resistors 210 and 212 to control the gain. A pair of load resistors 214 and 216 is connected between the drain of MESFETs 204 and 206 and a high voltage supply Vdd. Connected between the junction connections of the source of respective MESFETs 204 and 206 and source degeneration resistors 210 and 212 is a capacitor 218. Capacitor 218 is provided for effectively removing the photodetector jitter in accordance with the preferred embodiment.

The value of capacitor 218 is selected to minimize jitter. The capacitor 218 passes high slew rate signals more readily than low slew rate signals. The effect of the capacitor 218 is to bypass the gain limiting effects of the source degeneration resistors 210 and 212. As a result, differential

pair 202 is arranged to accentuate high slew rates over lower slew rates.

5 A pair of current source MESFETs 220 and 222 are connected between differential inputs IN and INC and ground via source resistor 224 and 226. A current source reference 230 is connected to the current source MESFETs 220 and 222. A MESFET 232, a drain resistor 234, a source resistor 236 and a capacitor 238 form the current source reference 230. MESFET 232 is connected between the high voltage Vdd and ground via drain and source resistors 234 and 236. Capacitor 238 is connected between the drain of MESFET 232 and ground. A gate of current source MESFETs 220 and 222 is connected to the gate of current source reference MESFET 232.

15 A current source MESFET 240 having a source resistor 242 is connected between the source degeneration resistors 210 and 212 and ground. A gate of current source MESFET 240 is connected to the gate of current source reference MESFET 232.

20 Output buffer stage 118 includes a first source follower pair 244 of MESFETs 246 and 248 having a respective gate connected to the drain of differential pair MESFETs 206 and 208 and a second source follower pair 250 of MESFETs 252 and 254 having a respective gate connected to the source of first source follower pair 244 of MESFETs 246 and 248. The first and second source follower pairs 244 and 250 provide a unity gain stage. A plurality of current source MESFETs 256, 258, 260 and 262 each having a respective source resistor 264, 266, 268 and 270 are connected to the first and second source follower pair MESFETs 246, 248, 252 and 254. A gate of current source MESFETs 256, 258, 260 and 262 is connected to the gate of current source reference MESFET 232. The source of MESFETs 252 and 254 of the second source follower pair 250 provide the differential outputs OUT and OUTC of the output buffer circuitry 114 of the fiber optic transceiver channel 100.

30 It should be understood that the present invention is not limited to the use of metal semiconductor field effect transistors (MESFETs) as shown in FIGS. 1 and 2. It should be understood that the fiber optic transceiver channel 100 including output buffer 118 of the preferred embodiment could

be implemented, for example, with bipolar transistors, N-channel field effect transistors or P-channel field effect transistors.

- 5 While the present invention has been described with reference to the details of the embodiments of the invention shown in the drawing, these details are not intended to limit the scope of the invention as claimed in the appended claims.